Product data sheet

1. General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a small and leadless ultra thin DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- · Exposed drain pad for excellent thermal conduction
- AEC-Q101 qualified

3. Applications

- · DC to DC conversion
- · High-speed line driver
- · High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	1						
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-10	-	10	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-3.6	Α
Static charac	teristics (per transistor)						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -3.6 \text{ A}; T_j = 25 \text{ °C}$		-	50	66	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		
2	G1	gate TR1	6 5 4	D1 D2
3	D2	drain TR2		
4	S2	source TR2	7 8	
5	G2	gate TR2		
6	D1	drain TR1		
7	D1	drain TR1	Transparent top view DFN2020-6 (SOT1118)	017aaa258
8	D2	drain TR2	DEN2020-0 (3011110)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMDPB55XPA		plastic, leadless thermal enhanced ultra thin small outline package; no leads; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1118			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMDPB55XPA	8N

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or			'		
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-10	10	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.6	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.3	Α
		V_{GS} = -4.5 V; T_{sp} = 25 °C		-	-9.3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-37	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			[1]	-	1.2	W
		T _{sp} = 25 °C		-	8.3	W
Per device			,			'
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	640	mW
			[1]	-	1.6	W
		T _{sp} = 25 °C		-	11	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode (per transistor)		•			
Is	source current	T _{amb} = 25 °C	[1]	-	-1.2	Α
Avalanche r	uggedness (per transistor)		•	'		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -0.65 A; DUT in valanche (unclamped)		-	4.4	mJ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

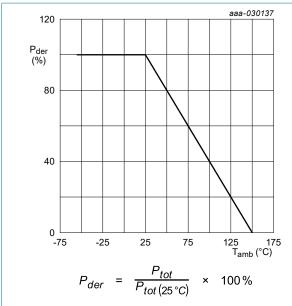


Fig. 1. Normalized total power dissipation as a function of ambient temperature

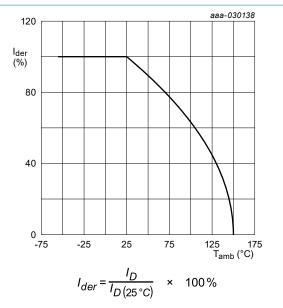


Fig. 2. Normalized continuous drain current as a function of ambient temperature

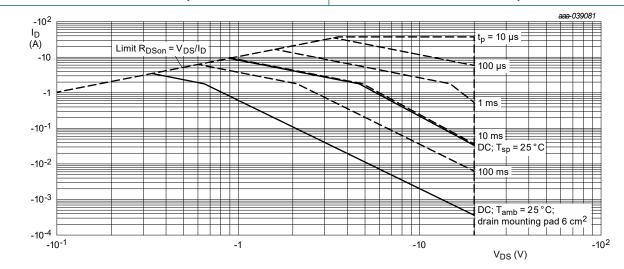


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

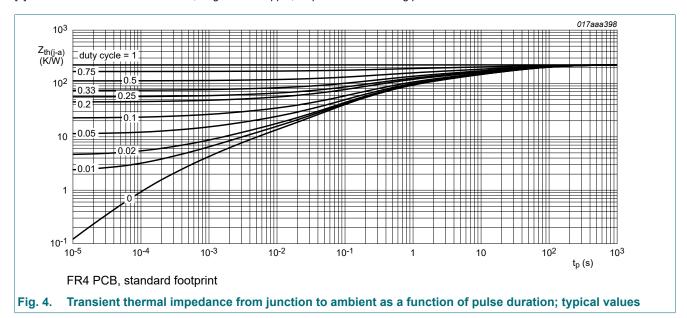
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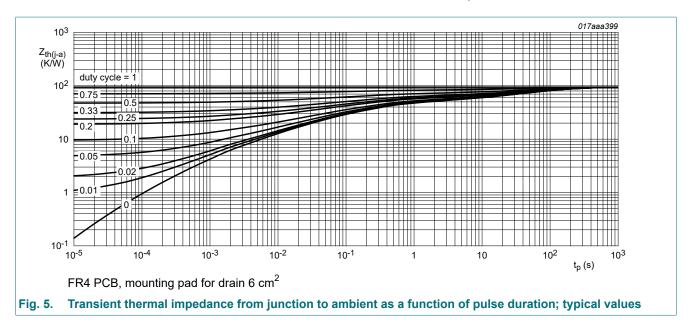
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	223	256	K/W
	junction to ambient		[2]	-	93	107	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W
Per device					1		
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	190	K/W
	junction to ambient		[2]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	11	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².





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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.47	-0.65	-1	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -3.6 \text{ A}; T_j = 25 \text{ °C}$	-	50	66	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -3.6 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	73	96	mΩ
		V_{GS} = -2.5 V; I_D = -2.6 A; T_j = 25 °C	-	62	87	mΩ
		V _{GS} = -1.8 V; I _D = -0.5 A; T _j = 25 °C	-	83	135	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -3.6 A; T_j = 25 °C	-	12	-	S
Dynamic ch	naracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -3.6 A; V_{GS} = -4.5 V;	-	8.8	13	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.2	-	nC
Q _{GD}	gate-drain charge		-	2.4	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	785	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	70	-	pF
C _{rss}	reverse transfer capacitance		-	62	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -3.6 A; V_{GS} = -4.5 V;	-	11	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	2	-	ns
t _{d(off)}	turn-off delay time	1	-	55	-	ns
t _f	fall time	1	-	135	-	ns
Source-dra	in diode (per transistor)		1	1		
V _{SD}	source-drain voltage	$I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
t _{rr}	reverse recovery time	$I_S = -2 \text{ A}; dI_S/dt = 60 \text{ A/}\mu\text{s}; V_{GS} = -4.5 \text{ V};$	-	14	-	ns
Q _r	recovered charge	V _{DS} = -20 V; T _j = 25 °C	-	4.8	-	nC

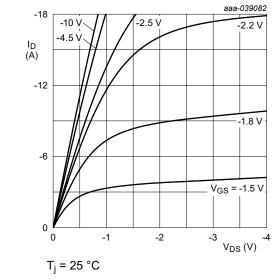


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

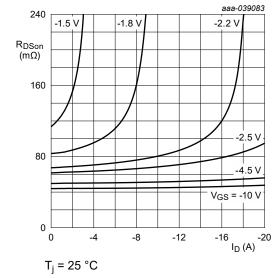


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

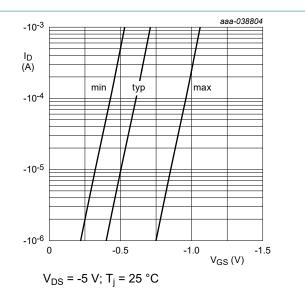


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

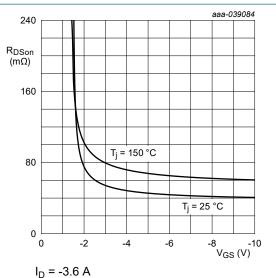


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

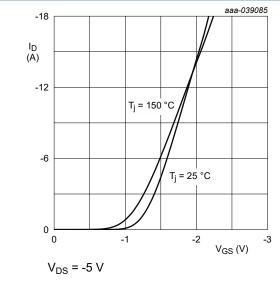


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

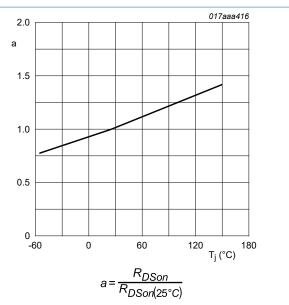


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

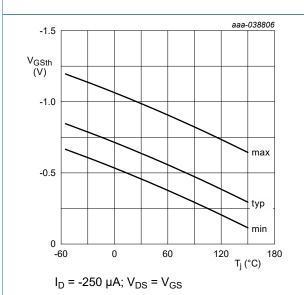
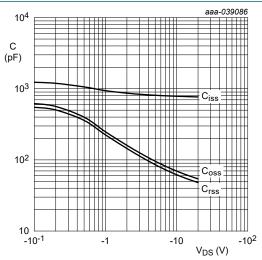


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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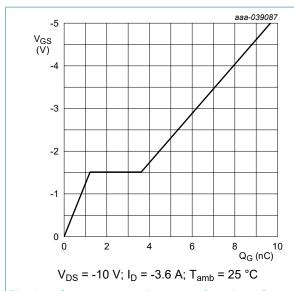


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

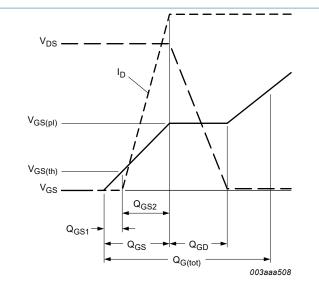


Fig. 15. Gate charge waveform definitions

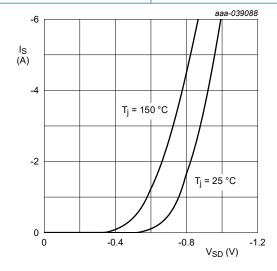
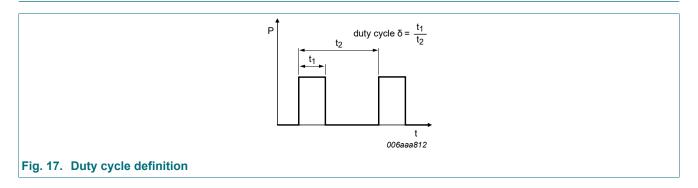


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information

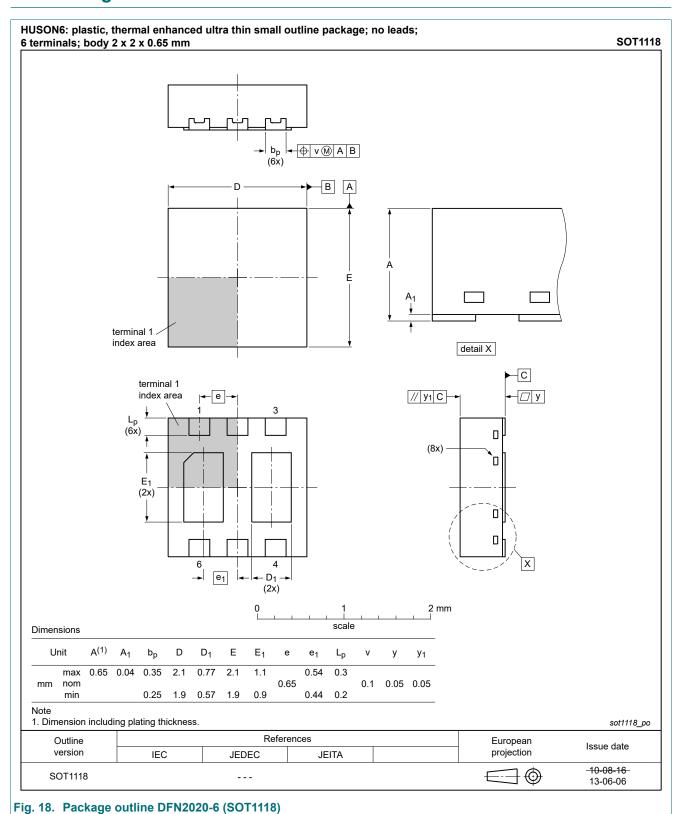


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

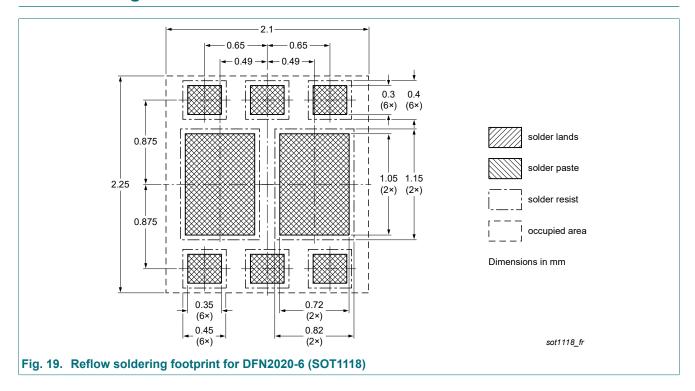
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMDPB55XPA v.1	20240318	Product data sheet	-	-

20 V, dual P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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